

ABSTRACT OF THE DISCLOSURE

An electrostatic discharge protection circuit is connected to a bonding pad and a pre-stage driver. The electrostatic discharge protection circuit includes a PMOS transistor and a NMOS transistor and both connect in series. A source/drain region of the PMOS transistor is connected to a system power source, and the gate electrode is connected to a pre-stage drive, and the other source/drain region is connected to a source/drain region of the NMOS transistor, which is also connected to the bonding pad. Another source/drain region of the NMOS transistor is ground. The gate electrode of the NMOS transistor receives an output of the pre-stage driver. Another PMOS transistor is connected to a capacitor and is also connected to the source/drain region of a system power source and the gate electrode of the NMOS transistor.